

• General Description

The CH100N04D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

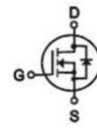
• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

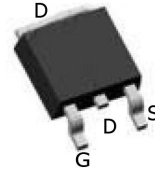
• Product Summary



$$V_{DS} = 40V$$

$$R_{DS(ON) Typ} = 3.6 m\Omega$$

$$I_D = 100A$$



TO-252

• Ordering Information:

Part NO.	CH100N04D
Marking	CH100N04D
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

• Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	100	A
	$I_{D@TC=75^\circ C}$	60	A
	$I_{D@TC=100^\circ C}$	54	A
Pulsed Drain Current ^①	I_{DM}	360	A
Total Power Dissipation($TC=25^\circ C$)	$P_{D@TC=25^\circ C}$	65	W
Total Power Dissipation($TA=25^\circ C$)	$P_{D@TA=25^\circ C}$	5.0	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy@ $L=0.1mH$	E_{AS}	150	mJ
Avalanche Current@ $L=0.1mH$	I_{AS}	55	A

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.67	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	75	°C/W
Soldering temperature, wavesoldering for 10s	T_{solder}	-	-	265	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1	1.6	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$		3.6	4.6	m Ω
		$V_{GS}=4.5V, I_D=10A$		4.8	6.3	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=15V, I_D=10A$				S
Source-drain voltage	V_{SD}	$I_S=20A$			1.2	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	3800	-	pF
Output capacitance	C_{oss}		-	274	-	
Reverse transfer capacitance	C_{rss}		-	215	-	

•Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DS}=15V$	-	73	-	nC
Gate - Source charge	Q_{gs}	$I_D=30A$	-	15	-	
Gate - Drain charge	Q_{gd}	$V_{GS}=20V$	-	16	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Typical Characteristics

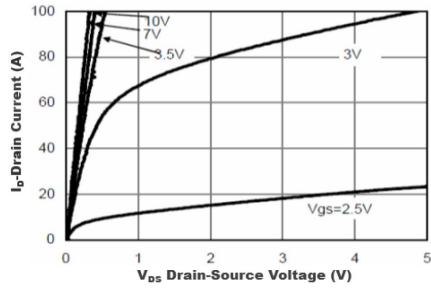


Figure1. Output Characteristics

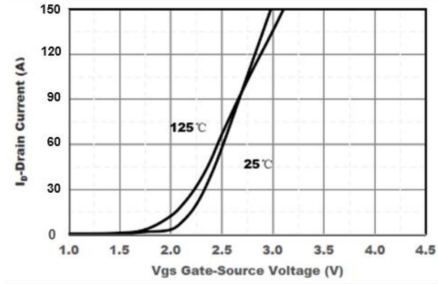


Figure2. Transfer Characteristics

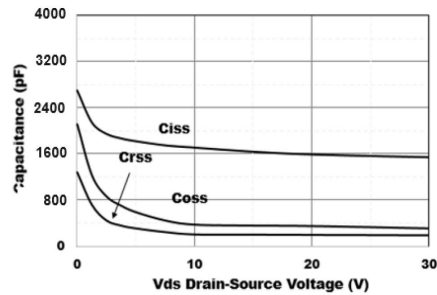


Figure3. Capacitance Characteristics

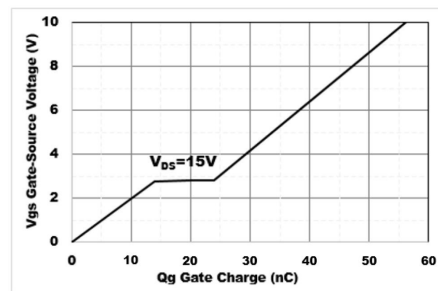


Figure4. Gate Charge

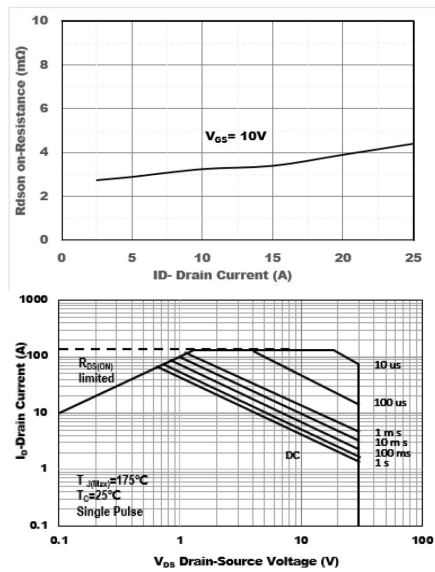


Figure7. Safe Operation Area

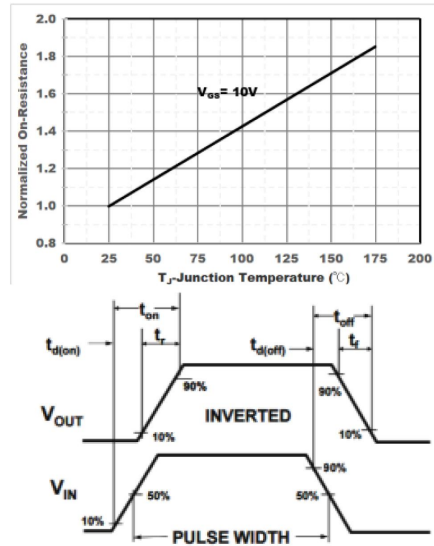


Figure8. Switching wave

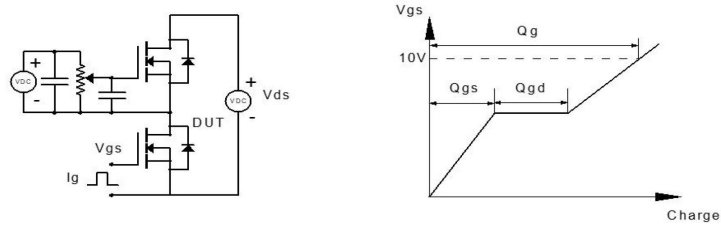


Figure 1: Gate Charge Test Circuit & Waveform

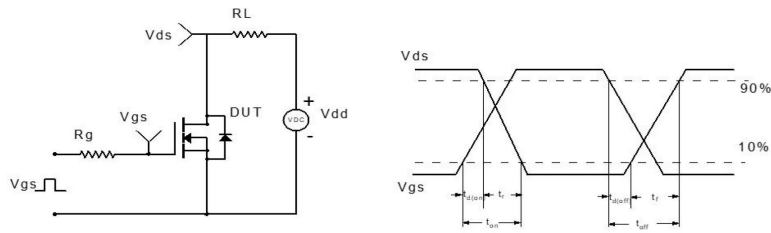


Figure 2: Resistive Switching Test Circuit & Waveform

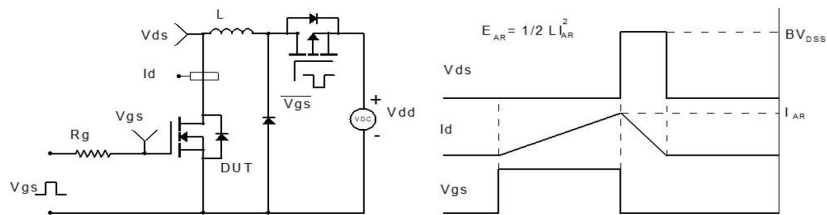


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

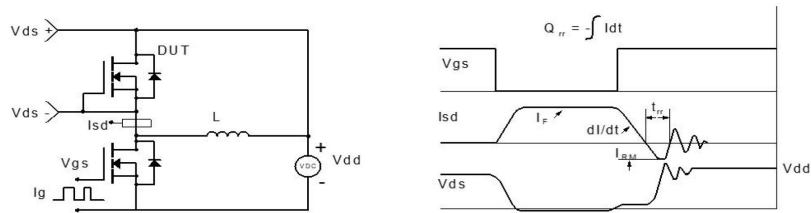
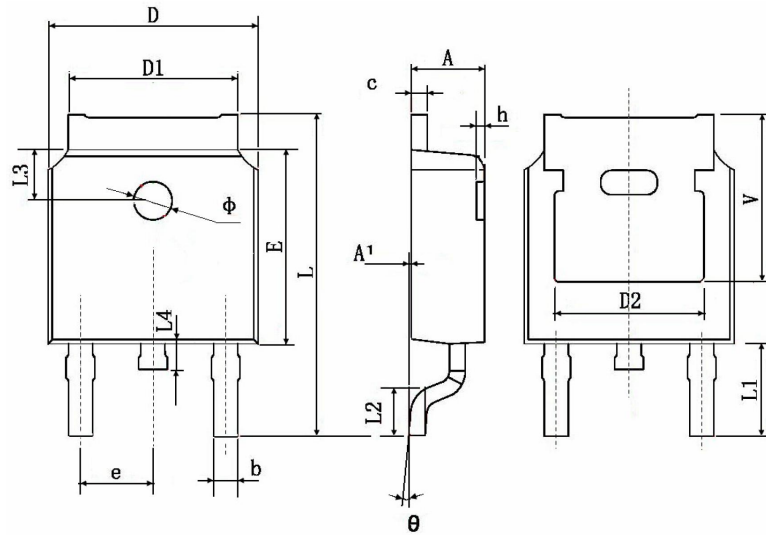


Figure 4: Diode Recovery Test Circuit & Waveform

●Dimensions (TO-252)


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	